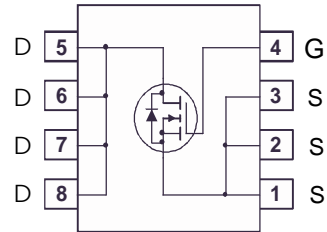


Features

- $R_{DS(ON)} = 23m\Omega$, $V_{GS} = 10V$, $I_D = 7.5A$
- $Q_g(tot) = 28nC$ (Typ.), $V_{GS} = 10V$
- Low Miller Charge
- Low Q_{RR} Body Diode
- Optimized efficiency at high frequencies
- UIS Capability (Single Pulse and Repetitive Pulse)



Applications

- DC/DC converters and Off-Line UPS
- Distributed Power Architectures and VRMs
- Primary Switch for 24V and 48V Systems
- High Voltage Synchronous Rectifier

MOSFET Maximum Ratings $T_A = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	100	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current		
	Continuous ($T_A = 25^\circ C$, $V_{GS} = 10V$, $R_{\theta JA} = 50^\circ C/W$)	7.5	A
	Continuous ($T_A = 100^\circ C$, $V_{GS} = 10V$, $R_{\theta JA} = 50^\circ C/W$)	4.8	A
	Pulsed	Figure 4	A
E_{AS}	Single Pulse Avalanche Energy (Note 1)	416	mJ
P_D	Power dissipation	2.5	W
	Derate above $25^\circ C$	20	mW/ $^\circ C$
T_J, T_{STG}	Operating and Storage Temperature	-55 to 150	$^\circ C$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient at 10 seconds (Note 3)	50	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient at 1000 seconds (Note 3)	85	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance, Junction to Case (Note 2)	25	$^\circ C/W$

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
B_{VDSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 80\text{V}$ $V_{GS} = 0\text{V}$	-	-	1	μA
		$T_C = 150^\circ\text{C}$	-	-	250	
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(TH)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	2	-	4	V
$R_{DS(ON)}$	Drain to Source On Resistance	$I_D = 7.5\text{A}, V_{GS} = 10\text{V}$	-	19	23	m Ω
		$I_D = 6.8\text{A}, V_{GS} = 4.5\text{V}$	-	24	28	
		$I_D = 7.5\text{A}, V_{GS} = 10\text{V},$ $T_C = 150^\circ\text{C}$	-	35	43	
Dynamic Characteristics						
C_{ISS}	Input Capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V},$ $f = 1\text{MHz}$	-	2015	-	pF
C_{OSS}	Output Capacitance		-	285	-	pF
C_{RSS}	Reverse Transfer Capacitance		-	70	-	pF
$Q_g(TOT)$	Total Gate Charge at 10V	$V_{GS} = 0\text{V to } 10\text{V}$	-	28	37	nC
$Q_g(TH)$	Threshold Gate Charge	$V_{GS} = 0\text{V to } 2\text{V}$	-	4	6	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DD} = 50\text{V}$ $I_D = 7.5\text{A}$ $I_g = 1.0\text{mA}$	-	10	-	nC
Q_{gs2}	Gate Charge Threshold to Plateau		-	6.8	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	6	-	nC
Switching Characteristics ($V_{GS} = 10\text{V}$)						
t_{ON}	Turn-On Time	$V_{DD} = 50\text{V}, I_D = 4\text{A}$ $V_{GS} = 10\text{V}, R_{GS} = 10\Omega$	-	-	51	ns
$t_{d(ON)}$	Turn-On Delay Time		-	14	-	ns
t_r	Rise Time		-	20	-	ns
$t_{d(OFF)}$	Turn-Off Delay Time		-	37	-	ns
t_f	Fall Time		-	27	-	ns
t_{OFF}	Turn-Off Time		-	-	96	ns
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Voltage	$I_{SD} = 7.5\text{A}$	-	-	1.25	V
		$I_{SD} = 4\text{A}$	-	-	1.0	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 7.5\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	55	ns
Q_{RR}	Reverse Recovered Charge	$I_{SD} = 7.5\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	90	nC

Notes:

- 1: Starting $T_J = 25^\circ\text{C}$, $L = 13\text{mH}$, $I_{AS} = 8\text{A}$.
- 2: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.
- 3: $R_{\theta JA}$ is measured with 1.0 in² copper on FR-4 board

Typical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

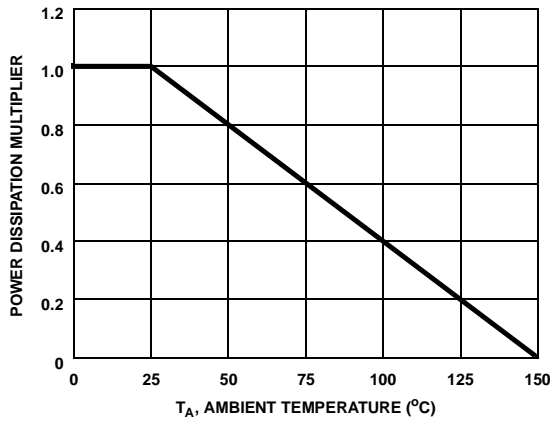


Figure 1. Normalized Power Dissipation vs Ambient Temperature

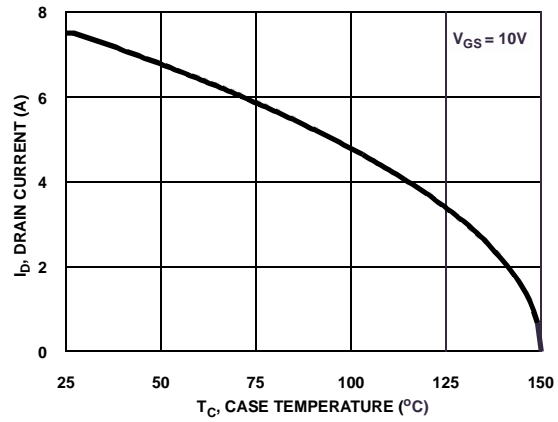


Figure 2. Maximum Continuous Drain Current vs Case Temperature

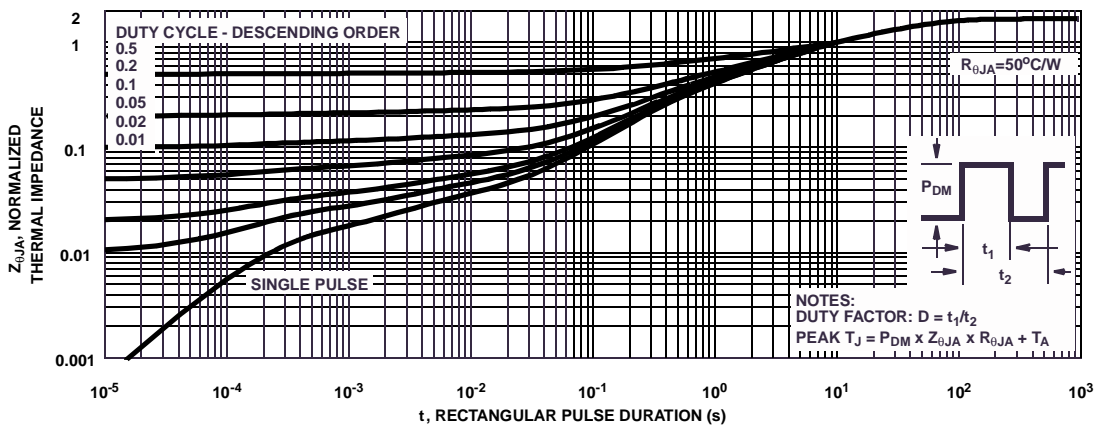


Figure 3. Normalized Maximum Transient Thermal Impedance

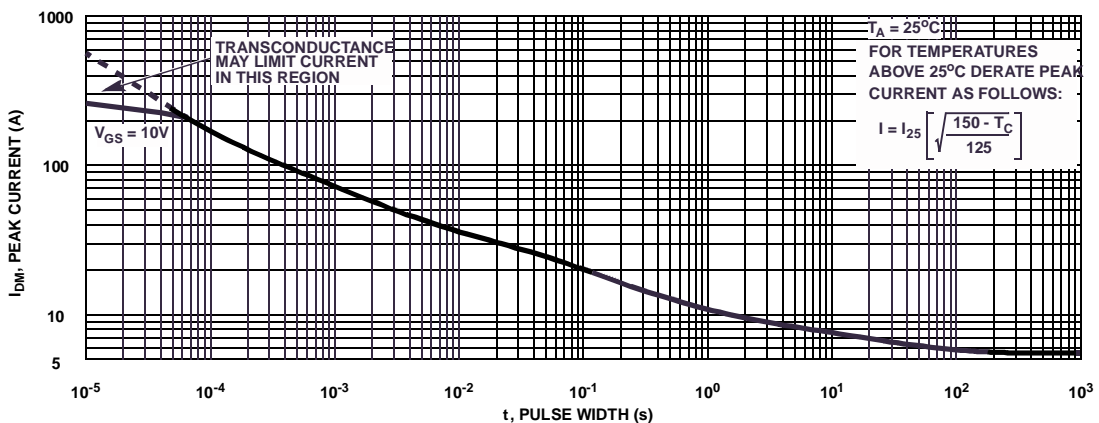


Figure 4. Peak Current Capability

Typical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

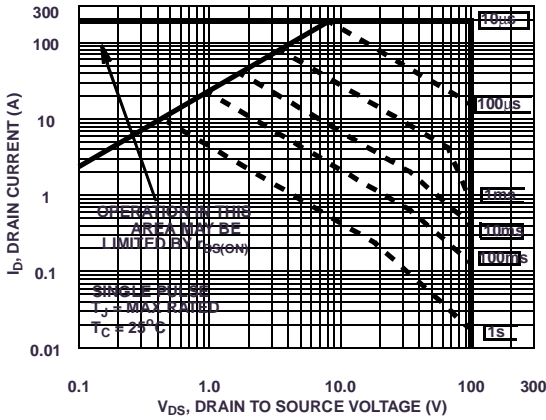


Figure 5. Forward Bias Safe Operating Area

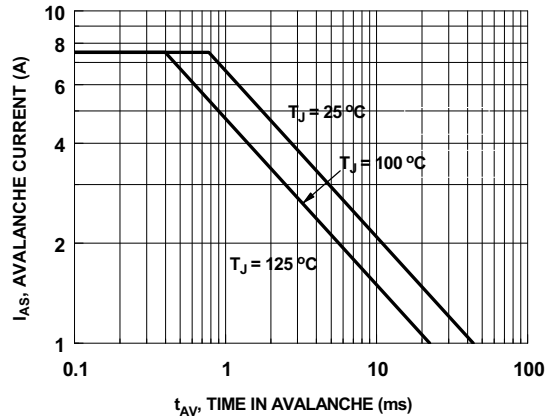


Figure 6. Unclamped Inductive Switching Capability

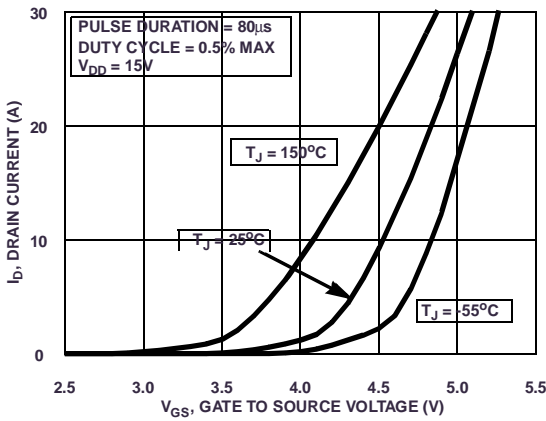


Figure 7. Transfer Characteristics

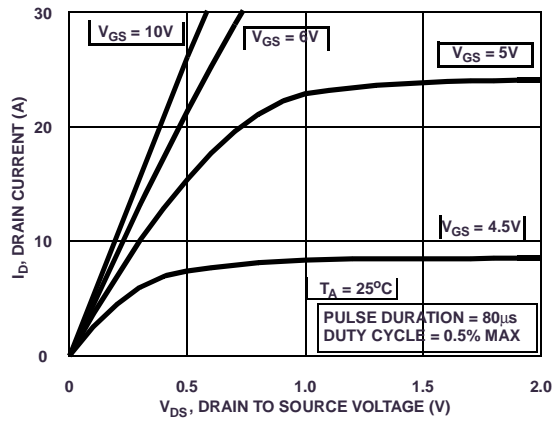


Figure 8. Saturation Characteristics

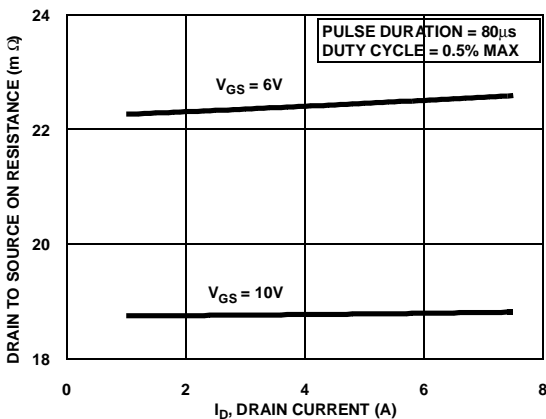


Figure 9. Drain to Source On Resistance vs Drain Current

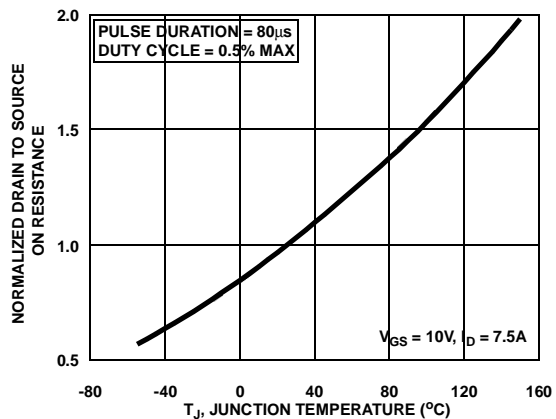


Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature

Typical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

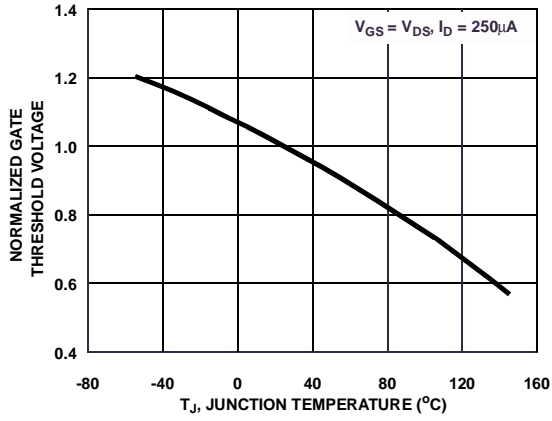


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

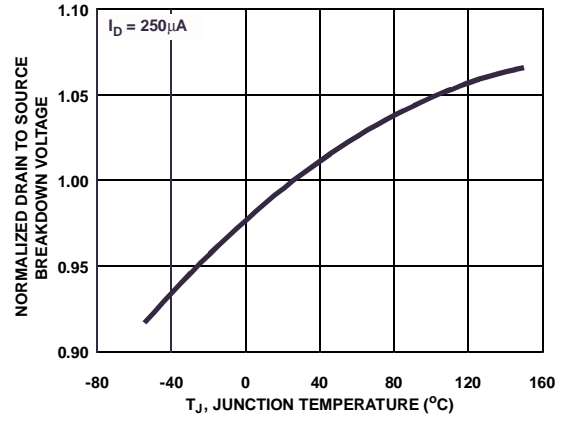


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

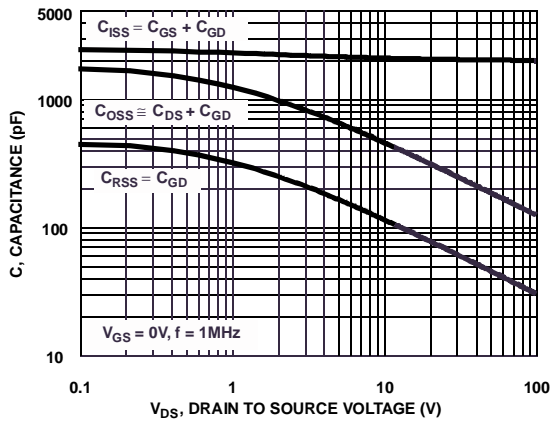


Figure 13. Capacitance vs Drain to Source Voltage

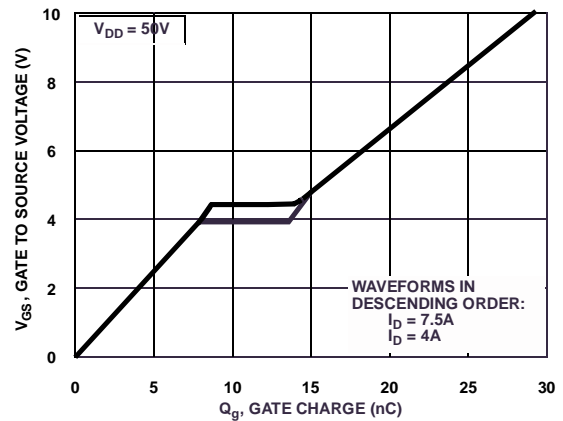
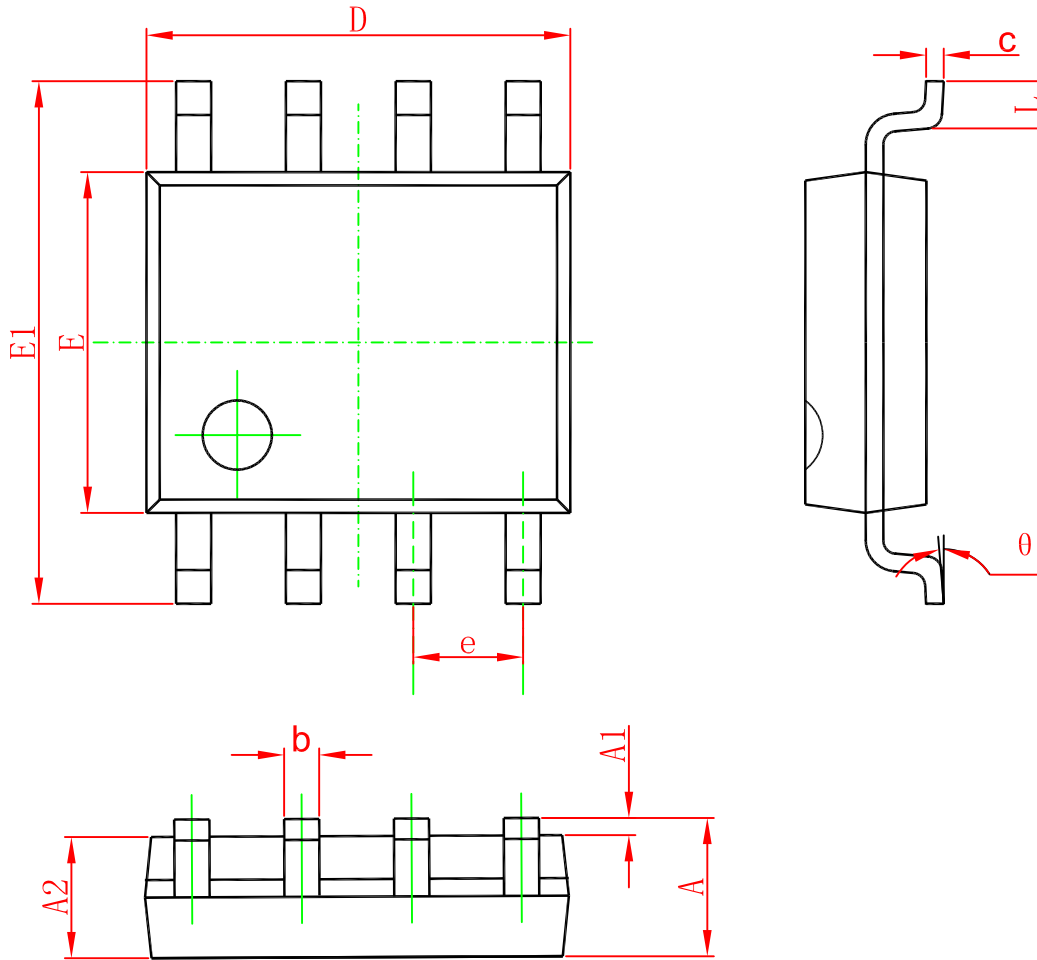


Figure 14. Gate Charge Waveforms for Constant Gate Currents

SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Ordering information

Order code	Package	Baseqty	Deliverymode
UMW FDS3672	SOP-8	3000	Tape and reel

单击下面可查看定价，库存，交付和生命周期等信息

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